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LOW NOISE, 15 GHz, COOLED, GAAsFET AMPLIFIER

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LOW NOISE, 15 GHz, COOLED, GaAsFET AMPLIFIER

S. Weinreb and R. Harris

I. Introduction

This report describes the testing and construction of 60 amplifiers for the VLA with the following specifications at a physical temperature of 15K:

| FREQUENCY GHz | NOISE (including isolator) | GAIN (including 5 to 10 dB pad) |
|------------------|-------------------------------|------------------------------------|
| 15.1 | < 57K | 19 <u>+</u> 1 dB |
| 15.4 | < 66K | 19 <u>+</u> 3 dB |
| 14.4 | < 106K | 19 <u>+</u> 3 dB |

The amplifier is incorporated with an input isolator, output attenuator (for matching), and a SMA to waveguide adaptor as shown in Figure 1. This configuration is designed to easily fit the existing VLA dewar and improve the system noise temperature from 300K to 100K.

Background information on the amplifier design is given in a paper [1] by Tomassetti, Weinreb and Wellington describing a similar 10.7 GHz amplifer and in a report [2] by Sierra describing noise parameter measurements and computer programs used for the amplifier design. The major characteristics of the design are as follows:

1) GaAs FET's in the 1.75 mm square package are used. Early experiments with chips gave similar results and it was believed that better reliability would be achieved with packaged devices.

2) A coaxial geometry with a round center conductor in a square groove as suggested by Tomassetti is used. The characteristic impedance of this



Fig. 1. Input isolator (lower left), amplifier, output 8 dB pad, and output coax-to-waveguide transition mounting plate. The isolator input connects via a short .141 coaxial cable to an input coax-to-waveguide transition which is part of a gapped waveguide thermal transition to 300K.



Fig. 2. Three-stage amplifier with cover removed. Input is at left and output and DC bias connector are at right.

geometry is given by Wheeler [3]. Tuning is accomplished by moving small $\lambda/4$ slugs on the center conductor and DC blocks are formed by enclosing the FET leads, cut to specified length, in Teflon tubing within a hollow center conductor. DC bias is provided by small wires, $\lambda/4$ long, soldered directly to the FET package. This configuration has been found to be reliable, mechanically stable, repeatable, and amenable to theoretical analysis.

3) The amplifier input and output return loss is reasonable (\sim 10 dB) but an input isolator and output attenuator are used to provide > 20 dB return loss. The FET source lead inductance is kept to a minimum.

II. Construction

The chassis is milled from copper stock and plated with 1.2 μ m of gold. A 7/64" carbide mill is useful for the rectangular slot. A thermostatically controlled hot plate, low power microscope, and a 60W, 700°F soldering iron with \sim 1 mm tip are needed for construction. The assembly procedure is as follows:

1) With chassis heated on a hot plate to 175-200°C, solder the input end plate to the chassis, all chip capacitors except the ATC111 0.8 pF gate bias bypass, and the ground wire posts utilizing Ersin SN62-.028 rosin filled, 2% silver solder. Clean chassis with flux remover and check all chip capacitor values with a capacitance meter.

2) Using the small soldering iron, solder chip resistors, bias resistors, and protection diodes with SN62 solder.

3) Using the hot plate again, but at a temperature of 100°-120°C, solder the ATC111 0.8 pF gate bias bypass capacitors using Alpha 20E2 solder and Superior #30 flux.

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4) Glue the rexolite support on interstage center conductors as shown in Figure 5 using Eastman 910 adhesive.

5) Trim the leads on the MGF1412-09 second-stage FET to 1.8 mm on both source leads and to the values given in Figure 3 for gate and drain leads. Solder #40 enameled-copper bias leads to the FET.

6) Install #22 Teflon tubing (OD = 0.94 mm, ID = 0.43 mm) in the center conductors cutting off the tubing 0.25 mm beyond the end of the center conductor. Install tuning slugs on center conductors checking for a firm, sliding fit.

7) Install second-stage FET together with both interstage networks into the chassis and fasten source lead champs.

8) Prepare MGF1412-10 third-stage FET as in paragraph 5), above, and install in chassis by bending the gate lead.

9) Using the hot plate at 200°C, solder the DC bias connector into the output end plate with SN62 solder. Solder #32 enameled copper bias wires to the connector pins using the small soldering iron and SN62 solder. Bolt the output end plate to the chassis and solder bias wires to chip capacitors.

10) Prepare and install the NE67383 first-stage FET as in paragraph 5), above.

11) Solder all FET bias wires using SN62 solder except the tie connection to the ATC111 gate bias bypass capacitor is made with 20E2 solder.

12) Install input and output SMA connectors complete with Teflon tubing and tuning slugs.

13) Apply a small amount of polystyrene cement to the FET lead to Teflon tubing interface points.

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Schematic of single amplifier stage with units of pF, ohms, and millimeters. All transmission lines are designated by their length (top) and characteristic impedance; and L2 tune the amplifier center frequency and are changed by moving $\lambda/4$ transformer first stage, MGF1412-09 in second stage, and MGF1412-10 in third stage. Lengths L1 The FET's are NE67383 in propagation velocity is c except for .72c in 390 lines. slugs. Fig. 3.

-7-



Fig. 4. Amplifier with coaxial components removed.



Fig. 5. Close-up view of sliding transformers (top), center conductor, and Teflon-tubing DC blocks.



Fig. 6. Middle-stage view of amplifier.



Fig. 7. Close-up view of FET, bias leads (#40 enameled copper wire), and 0.8 pF gate bypass capacitor. Note the Teflon tubing protruding from within center conductor and pressing against FET for mechanical stability.

III. Adjustment and Test

The test configuration for the amplifier is shown in Figures 8 and 9; this equipment is used in conjunction with an Apple computer, ADIOS A/D interface [4], and NOISE1 program to give data output as shown in Figure 10.

The accuracy of the low-noise temperature measurements is increased by utilizing a cooled 20 dB Narda Model 4779 attenuator at the amplifier input. By cooling this attenuator from 300K to 15K, the temperature added to the amplifier noise temperature of \sim 40K is decreased from 300K to 18K. The error due to noise source or detector-law inaccuracy is then reduced by a factor of (300 + 40)/(18 + 40) = 5.9.

The noise source, input coaxial line, attenuator cascade was calibrated at the isolator input connector by comparison with a NRAO liquid nitrogen and room temperature noise standard. This was performed with the test dewar open at 300K. The change in the attenuation value due to cooling from 300K to 15K was measured at DC and was an increase of $0.18 \pm .01$ dB for two Narda attenuators. This is approximately compensated by a decrease in the loss of the coaxial lines as determined from measurements described in a previous report [5]. An error of 0.1 dB in the noise source excess noise temperature ratio would produce an amplifier noise temperature error of 1.3K. The temperature of the cooled attenuator is monitored with a Lake Shore Cryotronics DG-400 sensor.

The amplifier is tuned at 300K for minimum noise at 15.1 GHz and for gain flatness. An initial bias of 5V, 5 mA; 5.5V, 10 mA; and 4V, 10 mA is used for the first, second and third stages respectively at 300K. These values were then optimized at 15K for minimum noise and gain within specifications;

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Fig. 8. Test configuration showing HP346B noise source (top, middle), low-loss coaxial thermal transition into dewar, Narda 20 dB attenuator with temperature sensor, Pamtech input isolator, amplifier under test, Narda 7 or 8 dB output attenuator, output transition, isolator, and test receiver.



Fig. 9. Test receiver consisting of an Avantek 2-8 GHz YIG-tuned oscillator, Aertech RX16000 frequency doubler, isolator, directional coupler to provide reflectometer source, and mixer-preamp for noise temperature measurements.



14.5

14.9

15.1

15.5



| 07:26.1 | 06/17/8 | 3 ZER0=7.8 | ADB=6 TF=30 | 10 -NOB=5 | .73 |
|---------|---------|------------|-------------|-----------|----------|
| F,GHZ | NOISE | GAINJOB | F,GHZ | NOISE | GAIN, DB |
| 14.4 | 541.7 | 11.2 | 14.5 | 458,2 | 12.6 |
| 14.6 | 408.3 | 12.7 | 14.7 | 375.7 | 12.6 |
| 14.8 | 352 | 12.5 | 14.9 | 341.3 | 12.2 |
| 15 | 332 | 11.6 | 15.1 | 341.4 | 11.5 |
| 15.2 | 333.5 | 11.3 | 15.3 | 345 | 11.1 |
| 15.4 | 356 | 10.8 | 15.5 | 386.5 | 10.3 |

Typical gain and noise temperature for an amplifier Fig. 10. including input isolator and output 7 dB attenuator at physical temperatures of 15K (top) and 300K.

1) 260, PAH-122, OPT BIAS, 7 DB PAD 14:16.6 06/16/83 TAU=54.7 TL0=42.9 @ 14950 GH=17.3 GH=21 T=11.5K 3.98/6.1/-.735 5.52/14.8/-1.07 4/9.7/-1.011

15K

06/16/83 14 16 6 15900

. .

73 51.1

43.3 47.4 53.6

59.6

. . . **.**

25DB

15DB

GAIN, DB

20.5

20.8

20.5

19.6

18.3

2008

5^{NQ8}

1008

θK

61

44.5

43.5

49.6

55.6

14.6

14.8 15 15.2

15.4

13900

21

20.7

19.8

19.4

19

1

٠

14:27.4 06/16/83 2ER0=7.8 ADB=6 TF=15.4 -NDB=5.73 F.GHZ NOISE GAIN.DB F.GHZ NOISE GAIN 14.4 89.8 17.3 14.5 73 20.5

typical final values were 4V, 5 mA; 5.5V, 15 mA; and 4V, 8 mA. The amplifier gain including a 7 dB pad is typically 12 dB at 300K and 19 dB at 15K as shown in Figure 10. The typical improvement in noise temperature is a factor of ~ 8 .

A large variation of cold noise temperature with the NE67383 transistor batch was observed. An initial batch of 20 averaged 35K at optimum frequency; a second batch 40K; and the third batch 47K. The lowest noise temperature was 31K and \sim 15% of the transistors gave noise temperatures > 50K and were rejected. Early tests with the NE13783 produced noise temperatures above 60K.

REFERENCES

- G. Tomassetti, S. Weinreb, and K. Wellington, "Low-Noise 10.7 GHz Cooled GaAs FET Amplifier," <u>Electronics Letters</u>, vol. 17, no. 25/26, December 10, 1981, pp. 949-951.
- [2] M. Sierra, "15 GHz Cooled GaAsFET Amplifier-Design Background Information," NRAO Electronics Division Internal Report No. 229, June 1982.
- [3] H. A. Wheeler, "Transmission-Line Impedance Curves," <u>Proc. IRE</u>, vol. 38, no. 12, December 1950, pp. 1400-1403.
- [4] G. Weinreb and S. Weinreb, "ADIOS Analog-Digital Input Output System for Apple Computer," NRAO Electronics Division Internal Report No. 212, April 1981.
- [5] S. Weinreb, "Cryogenic Performance of Microwave Terminations, Attenuators, Absorbers, and Coaxial Cable," NRAO Electronics Division Internal Report No. 223, January 1982.

PARTS LIST Ku-Band FET Amp (15.1 GHz)

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| ITEM | QUANTITY | REF. DESIG. | DESCRIPTION | MFG. | PART NUMBER |
|--------------|----------|----------------|---------------------------------------|-------------------------|----------------------|
| 1 | 1 | | 15 GHz FET amplifier schematic | NRAO | A2.613S-01 |
| 2 | 1 | | Chassis | NRAO | D2.613M-73, sht. 1 |
| ŝ | | | Chassis details | NRAO | C2.613M-73, sht. 2 |
| 4 | 1 | | Amplifier cover | NRAO | C2.613M-70 |
| 5 - 5 - 5 | 9 | | Transistor strap | NRAO | B2.613M-71 |
| 9 | 1 | | Output end plate | NRAO | B2.613M-77 |
| | . 1 | | Input end plate | NRAO | B2.613M-78 |
| 8 | 4 | | Transformer slug (15 ohm) | NRAO | B2.613M-72 |
| 6 | 1 | | Transformer slug (26 ohm) | NRAO | B2.613M-72 |
| 10 | 1 | | Transformer slug (22 ohm) | NRAO | B2.613M-72 |
| 11 | 2 | | Interstage support | NRAO | B2.613M-75 |
| 12 | 2 | | Interstage inner conductor | NRAO | B2.613M-76 |
| 13 | 1 | | Mounting plate with output transition | NRAO | C2.613M-81 |
| 14 | 1 | | Input SMA modification | Omni-Spectra (modified) | 204CC/NRAO B2.613M79 |
| 15 | -1 | | Output SMA modification | Omni-Spectra (modified) | 204CC/NRAO B2.613M80 |

Appendix I.A

| | | | | | | -16- | | | | | | | r | r | r |
|----------------|---------------|-----------------|------------------------------------|------------------|-------------------|------------------|-----------------------------------|--------------------------------|------------------------|---|---------------------------------|---------------------------------|--------------------------------|--------------------------------|---------------------------------|
| PART NUMBER | 201-1A | ER-7S-6 | AWG-24 -LW | NE67383 | MGF-1412-09 | MGF-1412-10 | 8046 | 8055 | 97-221-A | | | | | | |
| MFG. | 0mn1-Spectra | Micro-Tech | Alpha | NEC | Mitsubishi | Mitsubishi | Belden | Belden | Instrument Specialties | - | All-Metal | All-Metal | All-Metal | All-Metal | All-Metal |
| DESCRIPTION | SMA connector | Power connector | λ/4 transformer dielectric, Teflon | FET, first stage | FET, second stage | FET, third stage | FET bias leads, 40 AWG T2 Beldure | Bias wires, 30 AWG SGL-Beldsol | Finger stock | 0-80 x 3/16 Filister HD screws (goldplated) | 4-40 x 3/16 socket HD SS screws | 4-40 x 5/16 socket HD SS screws | 2-56 x 1/2 socket HD SS screws | 2-56 x 1/4 socket HD SS screws | 2-56 x 3/16 socket HD SS screws |
| REF. DESIG. | | | | | | | | | | | | | | | |
| QUANTITY | 4 | | ور | 1 | Ч | 1 | 9 | 9 | 2 | 9 | 8 | 3 | 2 | 4 | 2 |
| ITEM | 16 | 17 | 18 | 19 | 20 | 21 | 22 | 23 | 24 | 25 | 26 | 27 | 28 | 29 | 30 |

Appendix I.B

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PARTS LIST

Ku-Band FET Amp (15.1 GHz)

| | | F | | | |
|------------------------------|------------------------|------------------------|--------------|-------------------------|-----------------|
| REF. DESCRIPTION DESCRIPTION | REF. DESCRIPTION | DESCRIPTION | | MFG. | PART NUMBER |
| 3 .8 pf chip capacito | .8 pf chip capacito | .8 pf chip capaciton | | ATC | 111TBA0R8B100AP |
| 6 . 8 pf chip capacitor | .8 pf chip capacitor | .8 pf chip capacitor | | ATC | 100A0R8CP50 |
| 6 16 pf chip capacitor | 16 pf chip capacitor | 16 pf chip capacitor | | ATC | 100A160CP50 |
| 6 680 pf chip capacito | 680 pf chip capacito | 680 pf chip capacito | ц | ATC | 100B681KP50X |
| 6 50 ohm chip resistor | 50 ohm chip resistor | 50 ohm chip resistor | | Mini-Systems, Inc. | WA13PG-500J-S |
| 3 49.9 ohm 1/8W metal f | 49.9 ohm 1/8W metal f | 49.9 ohm 1/8W metal f | ilm resistor | Corning | RLR05C-49R9-FR |
| 3 1000 ohm 1/8W metal fi | 1000 ohm 1/8W metal fi | 1000 ohm 1/8W metal fi | Llm resistor | Corning | RLR05C-1001-FR |
| 3 Diode zener | Diode zener | Diode zener | | Motorola | 1N4099 |
| 3 Diode zener | Diode zener | Diode zener | | Motorola | 1N821 |
| 1 7 dB attenuator DC-18 | 7 dB attenuator DC-18 | 7 dB attenuator DC-18 | GHz | Narda | 4779-7 |
| 1 Cooled isolator | Cooled isolator | Cooled isolator | | PamTech | PTC-2021M |
| .141 semi-rigid coax, | .141 semi-rigid coax, | .141 semi-rigid coax, | 50 ohm | Uniform Tubes | UT-141A |
| Polystyrene Q-dope | Polystyrene Q-dope | Polystyrene Q-dope | | GC Electronics | #37–2 |
| 910 adhesive | 910 adhesive | 910 adhesive | | Permabond International | 910 |
| Solder B20E2, .032 di | Solder B20E2, .032 di | Solder B20E2, .032 di | a. | Alpha Metals | B20E2032 |

Appendix I.C

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Ku-Band FET Amp (15.1 GHz) PARTS LIST

| - | | | | | | -18- | | | r | | r | r |
|---|----------------|-------------------|----------------------|--------------------|--|------|------|--|-------|---------|---|---|
| | PART NUMBER | SN62028 | #30 | #1544 | | | - | | | | | |
| | MFG. | Ersin | Superior Flux & Mfg. | Kester | | | | | | | | |
| | DESCRIPTION | Solder, 2% silver | Flux, Super-Safe | Flux, rosin liquid | | | | | | | | |
| | REF. DESIG. | | | | | | | | | | | |
| | QUANTITY | | | | | | | | | | | |
| | TEM | 46 | 47 | 48 | | | | | | | | |

Ku-Band FET Amp (15.1 GHz)

PARTS LIST

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Appendix II.A























Appendix II.L

1-98692 220891-1